



DOCUMENT CHANGE REQUEST

DCR number		1602		Changes required for: General		Originator: Steve Thacker	
Date: 2024/01/12				Date sent: 2023/10/06		Organisation: ESCC Executive Secretariat	
Status: IMPLEMENTED							
Title:	TRANSISTORS, POWER, MOSFET, N-CHANNEL, RAD-HARD BASED ON TYPE STRH100N6						
Number:	5205/022		Issue:	8			
Other documents affected:							
Page:							
15							
Paragraph:							
2.12.2							
Original wording:							
Source-to-Drain Diode Forward Voltage, VSD, Drift Value limit: ±5%							
Proposed wording:							
Source-to-Drain Diode Forward Voltage, VSD, Drift Value limit: ±15%							
See attached spec mark-up for details.							
Justification:							
This DCR is raised on behalf of Manufacturer STM.							
STM justification: The latest TID result showed a drift around 10% on wafers 8 inch on VSD test. In order to accept the wafers 8 inch, the drift value +-5% should be changed to +-15% for VSD.							

Attachments:
escc5205022iss_draft_9_in_review.docx
Modifications:
N/A
Approval signature:

Date signed:
2024-01-12